



PATENT
Attorney Docket No. 98124x205843

7A
3/11/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Wang et al.

Application No. 09/636,246

Group Art Unit: unassigned

Filed: August 10, 2000

Examiner: unassigned

For: POLISHING SYSTEM WITH
STOPPING COMPOUND AND
METHOD OF ITS USE

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

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MAR 06 2002
TC 1700

Dear Sir:

Prior to the examination of the above-identified patent application, please enter the following amendments and consider the following remarks.

AMENDMENTS

IN THE SPECIFICATION:

Replace the paragraph beginning at page 1, line 14, with:

A¹
Integrated circuits are made up of millions of active devices formed in or on a substrate, such as a silicon wafer. The active devices are chemically and physically connected into a substrate and are interconnected through the use of multilevel interconnects to form functional circuits. Typical multilevel interconnects comprise a first metal layer, an interlevel dielectric layer, and sometimes a third and subsequent metal layer. Interlevel dielectrics, such as doped and undoped silicon dioxide (SiO₂) and/or low-κ dielectrics, are used to electrically isolate the different metal layers.

Replace the paragraph beginning at page 5, line 19, with:

A²
The polishing additive can be any suitable phosphorous-containing compound. Suitable phosphorous-containing compounds include, for example, phosphates (e.g., pyrophosphates, tri-phosphates, condensed phosphates), phosphonic acids (e.g., mono-phosphonic acids, di-phosphonic acids, tri-phosphonic acids, poly-phosphonic acids), and salts of phosphonic acids. Preferred phosphorous-containing compounds include, for example, pyrophosphates, phosphonoacetic acid, ethylenediphosphonic acid,